

N-channel 100 V 16.3 mΩ standard level MOSFET in LFPAK

Rev. 4 — 27 September 2011

**Product data sheet** 

### 1. Product profile

#### 1.1 General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### **1.2 Features and benefits**

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power converters

#### 1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

# 1.4 Quick reference data

- Improved mechanical and thermal characteristics
- LFPAK provides maximum power density in a Power SO8 package
- Motor control
- Server power supplies

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	100	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; see <u>Figure 1</u>	-	-	51	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see Figure 2	-	-	117	W
Tj	junction temperature		-55	-	175	°C
Static cha	aracteristics					
$R_{DSon}$	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 100 °C; see <u>Figure 12</u>	-	-	29.3	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	12.7	16.3	mΩ

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#### N-channel 100 V 16.3 mΩ standard level MOSFET in LFPAK

Table 1.	Quick reference data continued					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic	characteristics					
$Q_{GD}$	gate-drain charge	$V_{GS} = 10 \text{ V}; \text{ I}_{D} = 30 \text{ A};$	-	16	-	nC
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 50 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	54	-	nC
Avalanch	e ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V}; \ T_{j(init)} = 25 \ ^{\circ}\text{C}; \\ I_{D} = 51 \ \text{A}; \ V_{sup} \leq 100 \ \text{V}; \\ \text{unclamped}; \ R_{GS} = 50 \ \Omega \end{array}$	-	-	87	mJ

## 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		_
2	S	source	mb	
3	S	source		
4	G	gate	a	
mb	D	mounting base; connected to drain	$\begin{array}{c} \hline \\ \hline \\ 1 \\ 2 \\ 3 \\ 4 \\ \end{array}$	mbb076 S

#### SOT669 (LFPAK; Power-SO8)

### 3. Ordering information

Table 3. Order	ing information		
Type number	Package		
	Name	Description	Version
PSMN016-100YS	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669

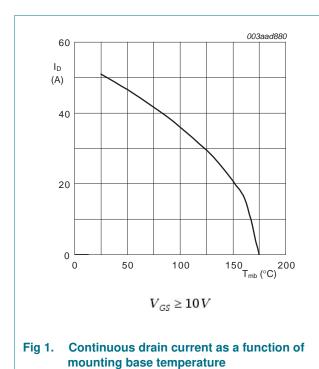
#### N-channel 100 V 16.3 m $\Omega$ standard level MOSFET in LFPAK

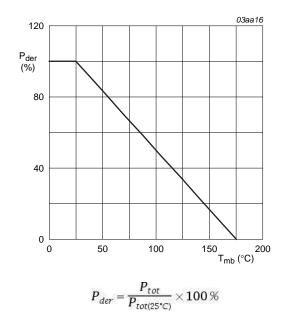
### 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	100	V
V <sub>DGR</sub>	drain-gate voltage	$T_j ≤ 175 °C; T_j ≥ 25 °C; R_{GS} = 20 kΩ$	-	100	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	$V_{GS}$ = 10 V; $T_{mb}$ = 100 °C; see <u>Figure 1</u>	-	36	А
		$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	-	51	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; see Figure 3	-	204	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	117	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
Source-dra	ain diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	51	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	204	А
Avalanche	ruggedness				
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \; V; \; T_{j(init)} = 25 \; ^{\circ}C; \; I_{D} = 51 \; A; \\ V_{sup} \leq 100 \; V; \; unclamped; \; R_{GS} = 50 \; \Omega \end{array}$	-	87	mJ
-					



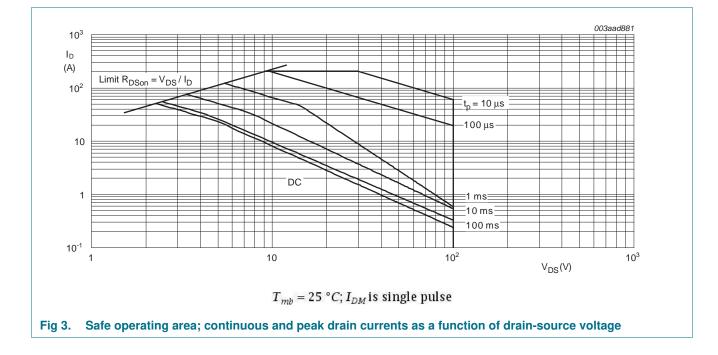




PSMN016-100YS Product data sheet

# **PSMN016-100YS**

#### N-channel 100 V 16.3 m $\Omega$ standard level MOSFET in LFPAK



10<sup>-1</sup>

10<sup>-2</sup>

10<sup>-3</sup>

0.1

0.05

single shot

N-channel 100 V 16.3 mΩ standard level MOSFET in LFPAK

ТП

Р

10

t<sub>p</sub> |--------- T

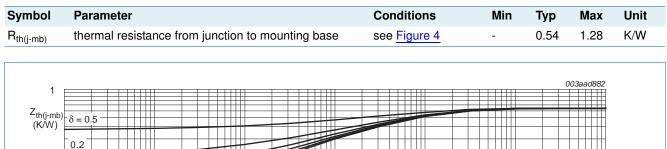
t<sub>p</sub> (s)

 $\delta = \frac{t_p}{T}$ 

1

### 5. Thermal characteristics

10<sup>-5</sup>



10<sup>-4</sup>

#

10<sup>-2</sup>

#### Table 5. Thermal characteristics



10<sup>-3</sup>

#### N-channel 100 V 16.3 m $\Omega$ standard level MOSFET in LFPAK

### 6. Characteristics

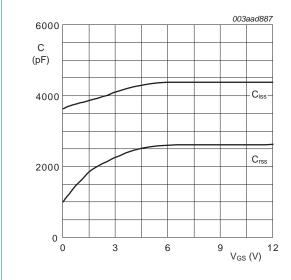
Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	90	-	-	V
	voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
$V_{GS(th)}$ gate-source threshold voltage	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; see <u>Figure 10</u>	1	-	-	V
	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; see <u>Figure 11</u> ; see <u>Figure 10</u>	2	3	4	V	
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; see <u>Figure 10</u>	-	-	4.7	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 125 °C	-	-	100	μA
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.04	2	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub> drain-source on-state resistance	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 100 °C; see <u>Figure 12</u>	-	-	29.3	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 175 °C; see <u>Figure 12</u>	-	28.7	45.6	mΩ
	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	12.7	16.3	mΩ	
R <sub>G</sub>	internal gate resistance (AC)	f = 1 MHz	-	0.6	1.5	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_{D} = 0 \text{ A};  V_{DS} = 0  \text{V};  V_{GS} = 10  \text{V}$	-	42	-	nC
		$I_D = 30 \text{ A}; \text{ V}_{DS} = 50 \text{ V}; \text{ V}_{GS} = 10 \text{ V};$	-	54	-	nC
Q <sub>GS</sub>	gate-source charge	see Figure 14; see Figure 15	-	11	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	$I_D = 30 \text{ A};  V_{DS} = 50 \text{ V};  V_{GS} = 10 \text{ V};$ see Figure 14	-	8	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	3.2	-	nC
Q <sub>GD</sub>	gate-drain charge	$I_D = 30 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	16	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	V <sub>DS</sub> = 50 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	4.2	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	2744	-	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{16}$	-	205	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	135	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 50 \text{ V}; \text{ R}_{L} = 1.7 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	19	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \ \Omega; T_j = 25 \ ^{\circ}C$	-	24	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	47	-	ns
t <sub>f</sub>	fall time		-	21	-	ns

# **PSMN016-100YS**

#### N-channel 100 V 16.3 mΩ standard level MOSFET in LFPAK

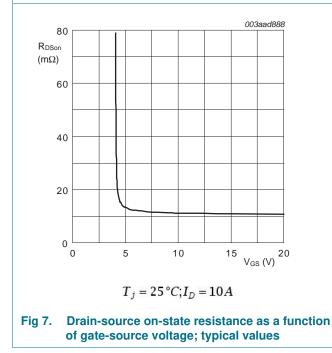
#### Table 6. Characteristics ...continued

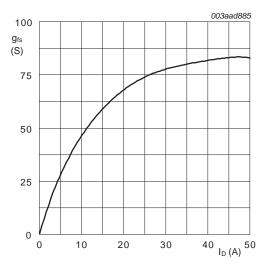
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drain diode						
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 15 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see <u>Figure 17</u>	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 10 \text{ A}; \text{ dI}_{S}/\text{dt} = 100 \text{ A}/\mu\text{s};$	-	56	-	ns
Qr	recovered charge	$V_{GS} = 0 V; V_{DS} = 50 V$	-	131	-	nC



 $V_{DS} = 0V; f = 1MHz$ 

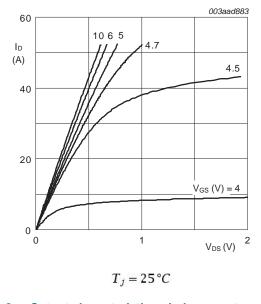






$$T_j = 25 \,^{\circ}C; V_{DS} = 10 \, V$$

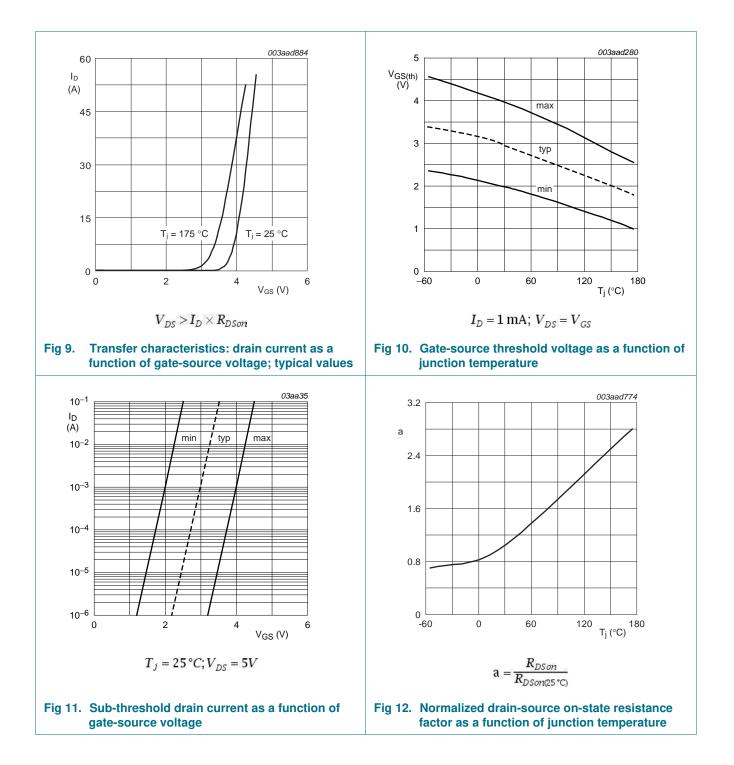






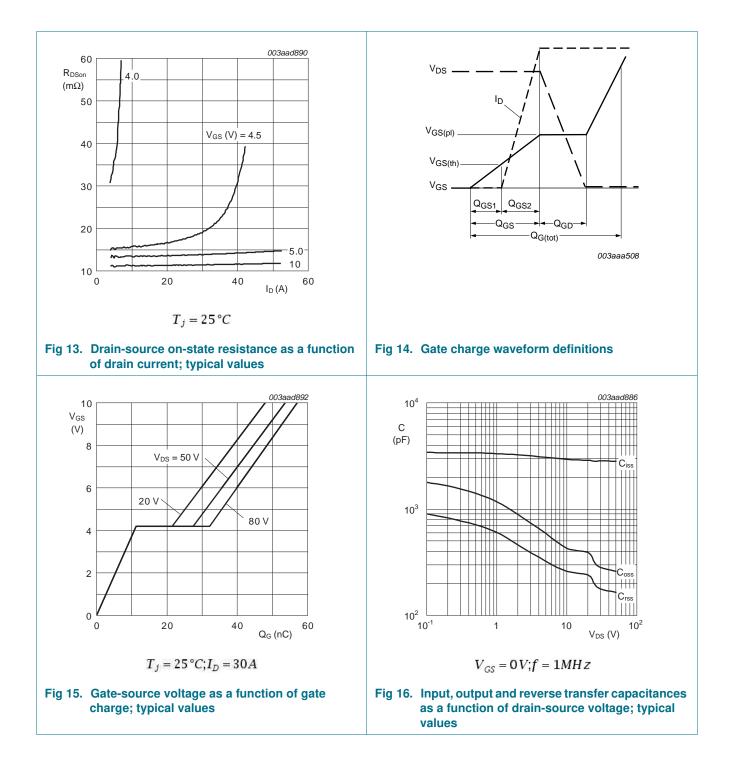
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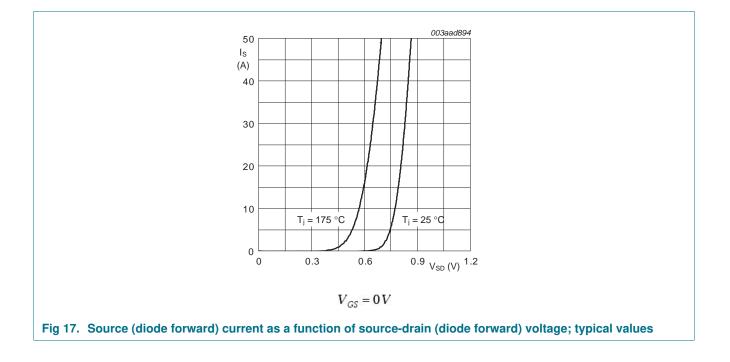
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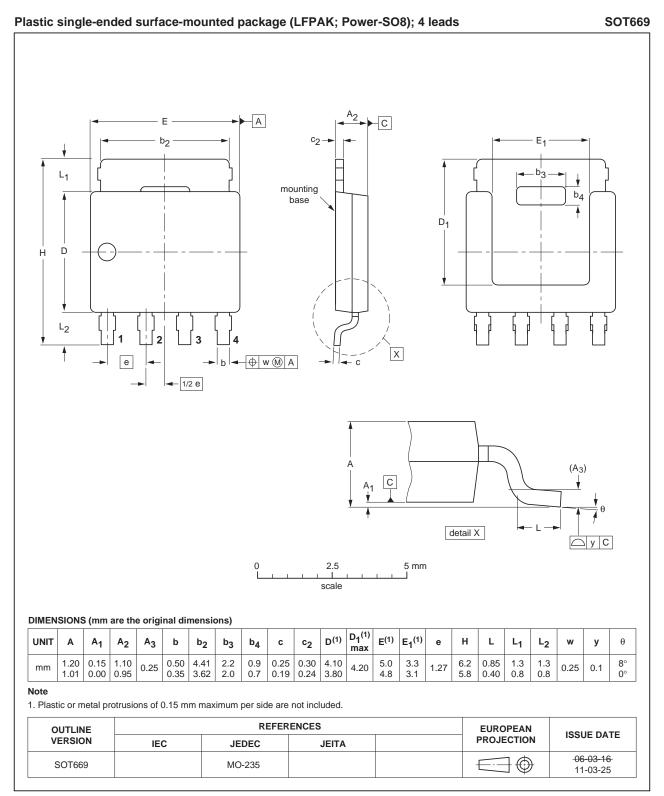
# **PSMN016-100YS**

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#### N-channel 100 V 16.3 mΩ standard level MOSFET in LFPAK

### 7. Package outline



#### Fig 18. Package outline SOT669 (LFPAK; Power-SO8)

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#### N-channel 100 V 16.3 mΩ standard level MOSFET in LFPAK

### 8. Revision history

#### Table 7.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN016-100YS v.4	20110927	Product data sheet	-	PSMN016-100YS v.3
Modifications:	<ul> <li>Various changes to</li> </ul>	o content.		
PSMN016-100YS v.3	20100330	Product data sheet	-	PSMN016-100YS v.2

### 9. Legal information

#### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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